

April 2009

MOCD211M Dual Channel Phototransistor Small Outline Surface Mount Optocouplers

Features

- UL recognized (File #E90700, Volume 2)
- VDE recognized (File #136616) (add option "V" for VDE approval, i.e, MOCD211VM)
- Minimum BV_{CEO} of 30 Volts guaranteed
- Standard SOIC-8 footprint, with 0.050" lead spacing
- Compatible with dual wave, vapor phase and IR reflow soldering
- High input-output isolation of 2500 V_{AC(rms)} guaranteed
- Compact dual channel optocoupler

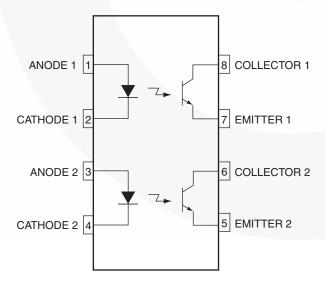
Applications

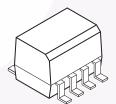
- Interfacing and coupling systems of different potentials and impedances
- General purpose switching circuits
- Monitor and detection circuits

Description

The MOCD211M device consists of two gallium arsenide infrared emitting diodes optically coupled to two monolithic silicon phototransistor detectors, in a surface mountable, small outline plastic package. It is ideally suited for high density applications and eliminates the need for through-the-board mounting.

Schematic





©2005 Fairchild Semiconductor Corporation MOCD211M Rev. 1.0.1

Absolute Maximum Ratings (T_A = 25°C Unless otherwise specified)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Rating	Value	Unit
EMITTER			
I _F	Forward Current – Continuous	60	mA
I _F (pk)	Forward Current – Peak (PW = 100µs, 120 pps)	1.0	А
V _R	Reverse Voltage	6.0	V
P _D	LED Power Dissipation @ T _A = 25°C	90	mW
	Derate above 25°C	0.8	mW/°C
DETECTOR			
V _{CEO}	Collector-Emitter Voltage	30	V
V _{ECO}	Emitter-Base Voltage	7.0	V
Ic	Collector Current-Continuous	150	mA
P _D	Detector Power Dissipation @ T _A = 25°C	150	mW
	Derate above 25°C	1.76	mW/°C
TOTAL DEVICE			
V _{ISO}	Input-Output Isolation Voltage (f = 60Hz, t = 1 min.)	2500	Vac(rms)
P_{D}	Total Device Power Dissipation @ T _A = 25°C	250	mW
	Derate above 25°C	2.94	mW/°C
T _A	Ambient Operating Temperature Range	-40 to +100	°C
T _{stg}	Storage Temperature Range	-40 to +150	°C

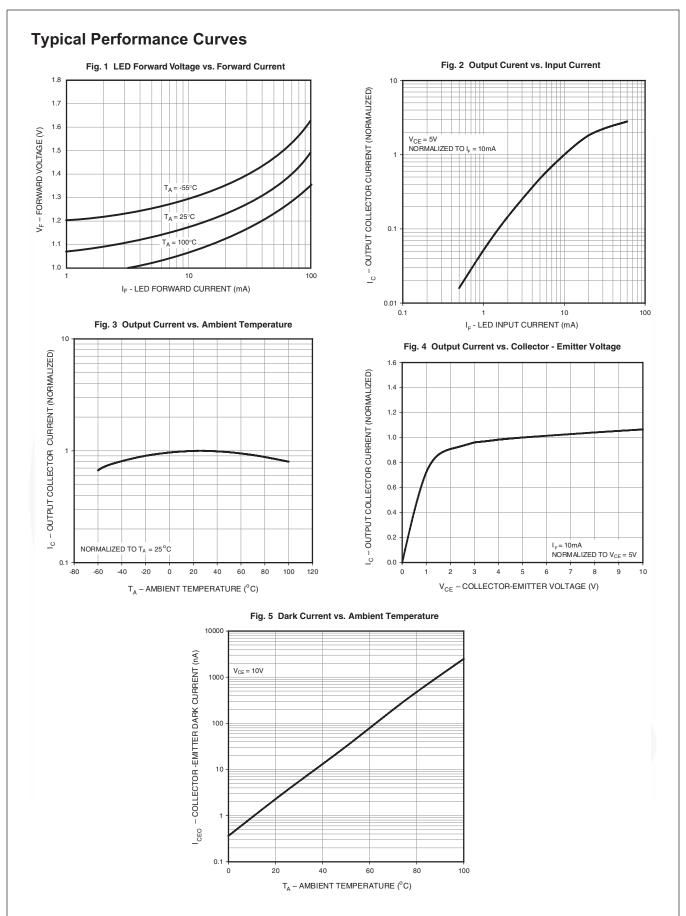
Electrical Characteristics (T_A = 25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.*	Max.	Unit
EMITTER				!		
V _F	Input Forward Voltage	I _F = 10mA		1.15	1.5	V
I _R	Reverse Leakage Current	V _R = 6.0V		0.001	100	μΑ
С	Capacitance			18		pF
DETECTO	R		1	1		
I _{CEO1}	Collector-Emitter Dark Current	V _{CE} = 10 V, T _A = 25°C		1.0	50	nA
I _{CEO2}		V _{CE} = 10 V, T _A = 100°C		1.0		μΑ
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 100μA	30	100		V
BV _{ECO}	Emitter-Collector Breakdown Voltage	Ι _Ε = 100μΑ	7.0	10		V
C _{CE}	Collector-Emitter Capacitance	f = 1.0MHz, V _{CE} = 0V		7.0		pF
COUPLED						
CTR	Current Transfer Ratio ⁽⁴⁾	I _F = 10mA, V _{CE} = 10V	20			%
V _{CE (sat)}	Collector-Emitter Saturation Voltage	I _C = 2.0mA, I _F = 10mA			0.4	V
t _{on}	Turn-On Time	$I_C = 2.0 \text{mA}, V_{CC} = 10 \text{V}, R_L = 100 \Omega$ (Fig. 6)		7.5		μs
t _{off}	Turn-Off Time	$I_C = 2.0 \text{mA}, V_{CC} = 10 \text{V}, R_L = 100 \Omega$ (Fig. 6)		5.7		μs
t _r	Rise Time	I_C = 2.0mA, V_{CC} = 10V, R_L = 100 Ω (Fig. 6)		3.2		μs
t _f	Fall Time	$I_C = 2.0 \text{mA}, V_{CC} = 10 \text{V}, R_L = 100 \Omega$ (Fig. 6)		4.7		μs
V _{ISO}	Isolation Surge Voltage ⁽¹⁾⁽²⁾⁽³⁾	f = 60Hz, t = 1 min.	2500			Vac(rms)
R _{ISO}	Isolation Resistance ⁽²⁾	V _{I-O} = 500V	10 ¹¹			Ω
C _{ISO}	Isolation Capacitance ⁽²⁾	$V_{I-O} = 0V$, $f = 1MHz$		0.2		pF

^{*}Typical values at T_A = 25°C

Notes:

- 1. Input-Output Isolation Voltage, $V_{\mbox{\scriptsize ISO}}$, is an internal device dielectric breakdown rating.
- 2. For this test, Pins 1, 2, 3 and 4 are common and Pins 5, 6, 7 and 8 are common.
- 3. V_{ISO} rating of 2500 $V_{AC(rms)}$ for t = 1 min. is equivalent to a rating of 3,000 $V_{AC(rms)}$ for t = 1 sec.
- 4. Current Transfer Ratio (CTR) = $I_C/I_F \times 100\%$.

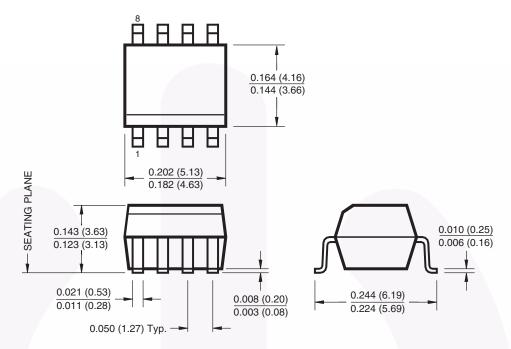


TEST CIRCUIT $V_{CC} = 10V$ INPUT PULSE OUTPUT OUTPUT PULSE $4djust \ l_F \ to \ produce \ l_C = 2mA$ $V_{CC} = 10V$ $0UTPUT \ PULSE$

Figure 6. Switching Time Test Circuit and Waveform

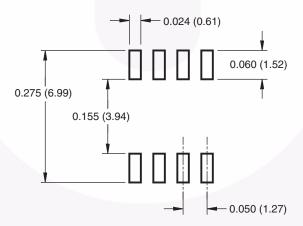
Package Dimensions

8-pin SOIC Surface Mount



Lead Coplanarity: 0.004 (0.10) MAX

Recommended Pad Layout



Dimensions in inches (mm).

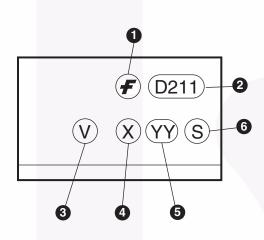
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Ordering Information

Option	Order Entry Identifier	Description	
V	V	VDE 0884	
R2	R2	Tape and reel (2500 units per reel)	
R2V	R2V	VDE 0884, Tape and reel (2500 units per reel)	

Marking Information

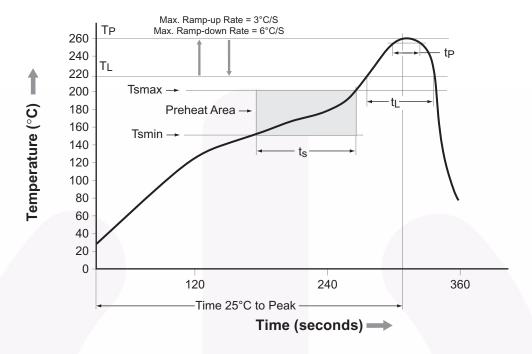


Defini	tions	
1	Fairchild logo	
2	Device number	
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)	
4	One digit year code, e.g., '8'	
5	Two digit work week ranging from '01' to '53'	
6	Assembly package code	

Carrier Tape Specifications 8.0 ± 0.10 -2.0 ± 0.05 → 3.50 ± 0.20 Ø1.5 MIN 1.75 ± 0.10 0.30 MAX 4.0 ± 0.10 → 0 ď 0 0 0 $\sqrt{}$ 5.5 ± 0.05 12.0 ± 0.3 8.3 ± 0.10 5.20 ± 0.20 0.1 MAX $Ø1.5 \pm 0.1$ 6.40 ± 0.20 User Direction of Feed

Dimensions in mm

Reflow Profile



Profile Freature	Pb-Free Assembly Profile		
Temperature Min. (Tsmin)	150°C		
Temperature Max. (Tsmax)	200°C		
Time (t _S) from (Tsmin to Tsmax)	60-120 seconds		
Ramp-up Rate (t _L to t _P)	3°C/second max.		
Liquidous Temperature (T _L)	217°C		
Time (t _L) Maintained Above (T _L)	60-150 seconds		
Peak Body Package Temperature	260°C +0°C / -5°C		
Time (t _P) within 5°C of 260°C	30 seconds		
Ramp-down Rate (T _P to T _L)	6°C/second max.		
Time 25°C to Peak Temperature	8 minutes max.		





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Definition of Terms			
Datasheet Identification	et Identification Product Status Definition		
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